



PIMD2

50 V, 100 mA NPN/PNP resistor-equipped double transistor;
R1 = 22 k Ω , R2 = 22 k Ω

13 March 2023

Product data sheet

1. General description

NPN/PNP Resistor-Equipped double Transistor (RET) in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

3. Applications

- Low current peripheral driver
- Controlling IC inputs
- Replaces general-purpose transistors in digital applications

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Per transistor							
V _{CEO}	collector-emitter voltage	open base	[1]	-	-	50	V
I _O	output current		[1]	-	-	100	mA
R1	bias resistor 1 (input)		[2]	15.4	22	28.6	k Ω
R2/R1	bias resistor ratio		[2]	0.8	1	1.2	

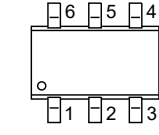
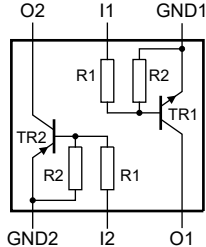
[1] For the PNP transistor with negative polarity.

[2] See section "Test information" for resistor calculation and test conditions.

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 22 k Ω , R2 = 22 k Ω

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND2	GND (emitter) TR2	 <p>TSOP6 (SOT457)</p>	 <p>006aab235</p>
2	I2	input (base) TR2		
3	O1	output (collector) TR1		
4	GND1	GND (emitter) TR1		
5	I1	input (base) TR1		
6	O2	output (collector) TR2		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PIMD2	TSOP6	plastic, surface-mounted package (SC-74; TSOP6); 6 leads	SOT457

7. Marking

Table 4. Marking codes

Type number	Marking code
PIMD2	M5

8. Limiting values

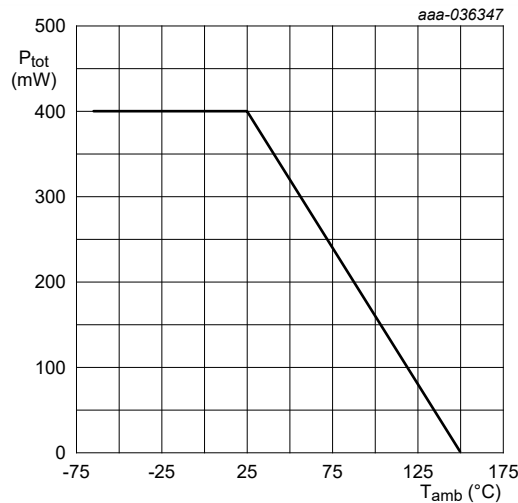
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transistor						
V_{CBO}	collector-base voltage	open emitter	[1]	-	50	V
V_{CEO}	collector-emitter voltage	open base	[1]	-	50	V
V_{EBO}	emitter-base voltage	open collector	[1]	-	10	V
V_I	input voltage	TR1 (NPN)		-10	40	V
		TR2 (PNP)		-40	10	V
I_O	output current		[1]	-	100	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$	[2]	-	250	mW
Per device						
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$	[2]	-	400	mW
T_j	junction temperature			-	150	°C
T_{amb}	ambient temperature			-55	150	°C
T_{stg}	storage temperature			-65	150	°C

[1] For the PNP transistor with negative polarity.

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided, 35 μm copper, tin-plated and standard footprint.



FR4 PCB, single-sided, 35 μm copper, tin-plated and standard footprint

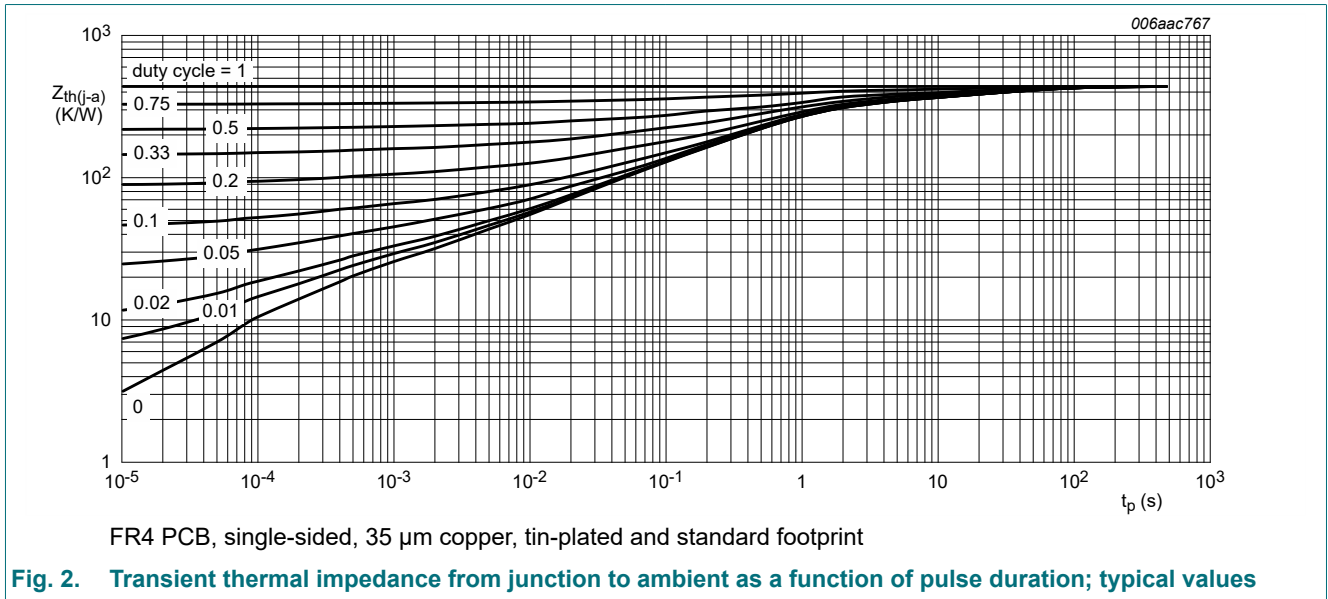
Fig. 1. Per device: Power derating curve

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Per transistor							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	500	K/W
Per device							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	313	K/W

[1] Device mounted on an FR4 PCB, single-sided, 35 μm copper, tin-plated and standard footprint.



10. Characteristics

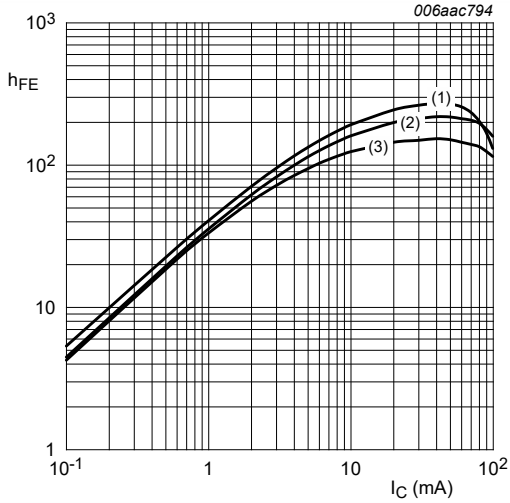
Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Per transistor							
$V_{(BR)CBO}$	collector-base breakdown voltage	$I_C = 100 \mu\text{A}$; $I_E = 0 \text{ A}$; $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$	[1]	50	-	-	V
$V_{(BR)CEO}$	collector-emitter breakdown voltage	$I_C = 2 \text{ mA}$; $I_B = 0 \text{ A}$; $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$	[1]	50	-	-	V
I_{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}$; $I_E = 0 \text{ A}$; $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$	[1]	-	-	100	nA
I_{CEO}	collector-emitter cut-off current	$V_{CE} = 30 \text{ V}$; $I_B = 0 \text{ A}$; $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$	[1]	-	-	100	nA
		$V_{CE} = 30 \text{ V}$; $I_B = 0 \text{ A}$; $T_j = 150 \text{ }^\circ\text{C}$	[1]	-	-	5	μA
I_{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}$; $I_C = 0 \text{ mA}$; $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$	[1]	-	-	180	μA
h_{FE}	DC current gain	$V_{CE} = 5 \text{ V}$; $I_C = 5 \text{ mA}$; $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$	[1]	60	-	-	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 10 \text{ mA}$; $I_B = 0.5 \text{ mA}$; $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$	[1]	-	-	150	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = 5 \text{ V}$; $I_C = 100 \mu\text{A}$; $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$	[1]	-	1.1	0.8	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = 0.3 \text{ V}$; $I_C = 5 \text{ mA}$; $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$		2.5	1.7	-	V
R1	bias resistor 1 (input)		[2]	15.4	22	28.6	kΩ
R2/R1	bias resistor ratio		[2]	0.8	1	1.2	
TR1 (NPN)							
C_c	collector capacitance	$V_{CB} = 10 \text{ V}$; $I_E = 0 \text{ A}$; $i_e = 0 \text{ A}$; $f = 1 \text{ MHz}$; $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$		-	-	2.5	pF
f_T	transition frequency	$V_{CE} = 5 \text{ V}$; $I_C = 10 \text{ mA}$; $f = 100 \text{ MHz}$; $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$	[3]	-	230	-	MHz
TR2 (PNP)							
C_c	collector capacitance	$V_{CB} = -10 \text{ V}$; $I_E = 0 \text{ A}$; $i_e = 0 \text{ A}$; $f = 1 \text{ MHz}$; $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$		-	-	3	pF
f_T	transition frequency	$V_{CE} = -5 \text{ V}$; $I_C = -10 \text{ mA}$; $f = 100 \text{ MHz}$; $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$	[3]	-	180	-	MHz

[1] For the PNP transistor with negative polarity.

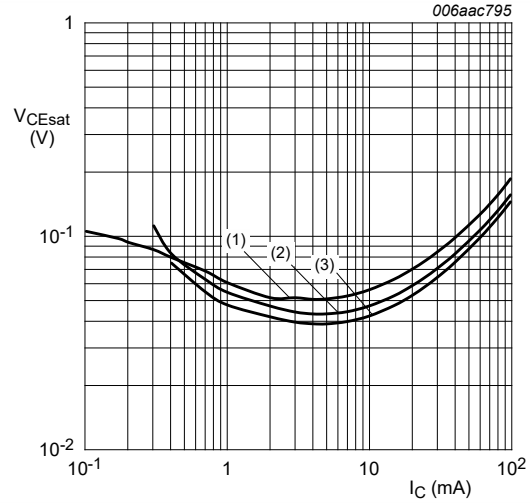
[2] See section "Test information" for resistor calculation and test conditions.

[3] Characteristics of built-in transistor



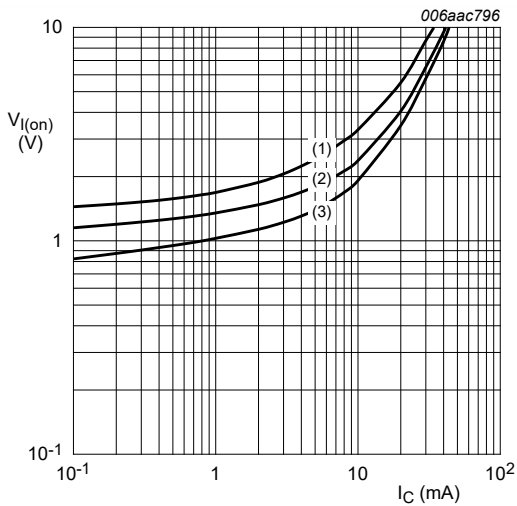
$V_{CE} = 5\text{ V}$
 (1) $T_{amb} = 100\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = -40\text{ °C}$

Fig. 3. TR1 (NPN): DC current gain as a function of collector current; typical values



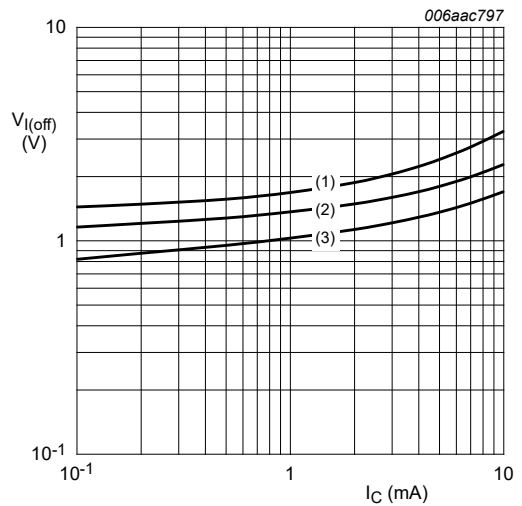
$I_C/I_B = 20$
 (1) $T_{amb} = 100\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = -40\text{ °C}$

Fig. 4. TR1 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values



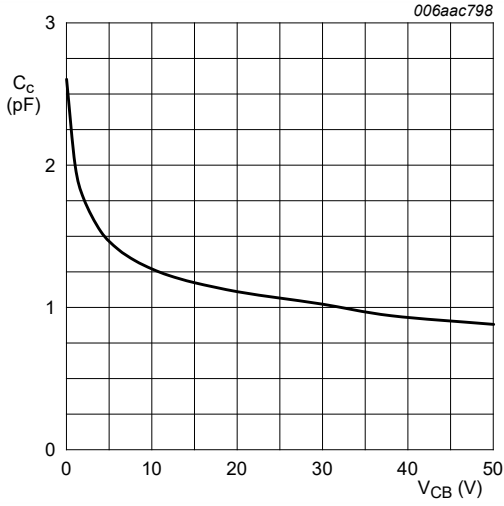
$V_{CE} = 0.3\text{ V}$
 (1) $T_{amb} = -40\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = 100\text{ °C}$

Fig. 5. TR1 (NPN): On-state input voltage as a function of collector current; typical values



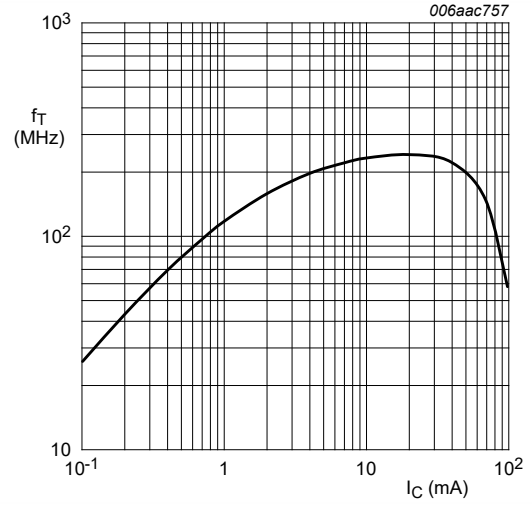
$V_{CE} = 5\text{ V}$
 (1) $T_{amb} = -40\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = 100\text{ °C}$

Fig. 6. TR1 (NPN): Off-state input voltage as a function of collector current; typical values



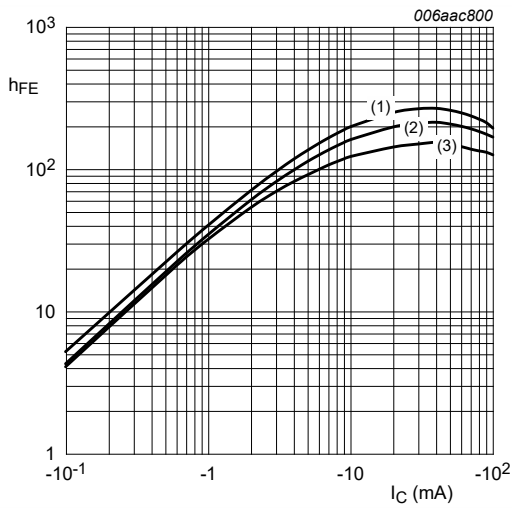
$f = 1 \text{ MHz}; T_{\text{amb}} = 25 \text{ }^\circ\text{C}$

Fig. 7. TR1 (NPN): Collector capacitance as a function of collector-base voltage; typical values



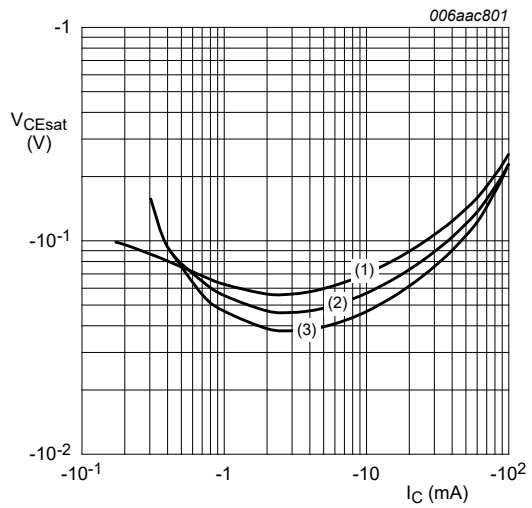
$f = 100 \text{ MHz}$
 $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$
 $V_{\text{CE}} = 5 \text{ V}$

Fig. 8. TR1 (NPN): Transition frequency as a function of collector current; typical values of built-in transistor



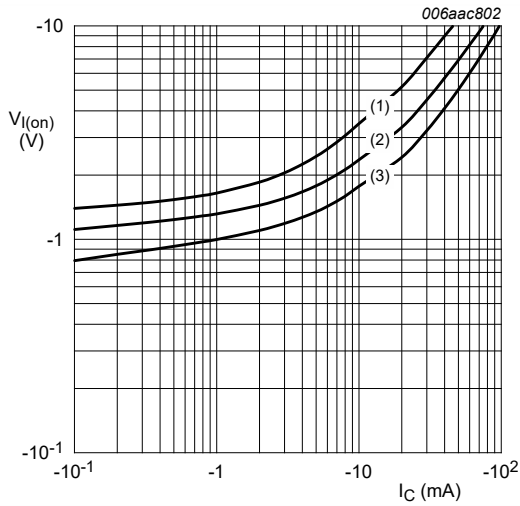
$V_{\text{CE}} = -5 \text{ V}$
 (1) $T_{\text{amb}} = 100 \text{ }^\circ\text{C}$
 (2) $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$
 (3) $T_{\text{amb}} = -40 \text{ }^\circ\text{C}$

Fig. 9. TR2 (PNP): DC current gain as a function of collector current; typical values



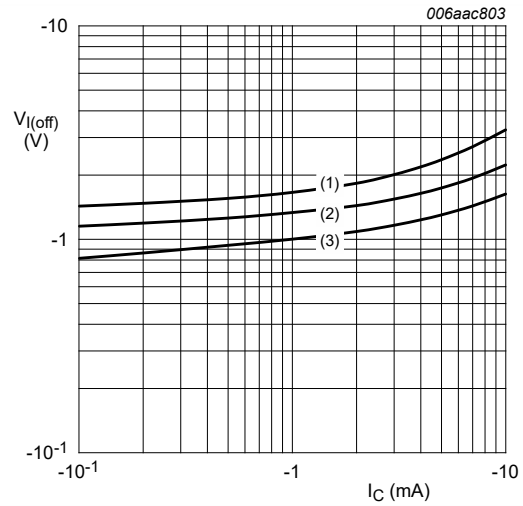
$I_{\text{C}}/I_{\text{B}} = 20$
 (1) $T_{\text{amb}} = 100 \text{ }^\circ\text{C}$
 (2) $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$
 (3) $T_{\text{amb}} = -40 \text{ }^\circ\text{C}$

Fig. 10. TR2 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values



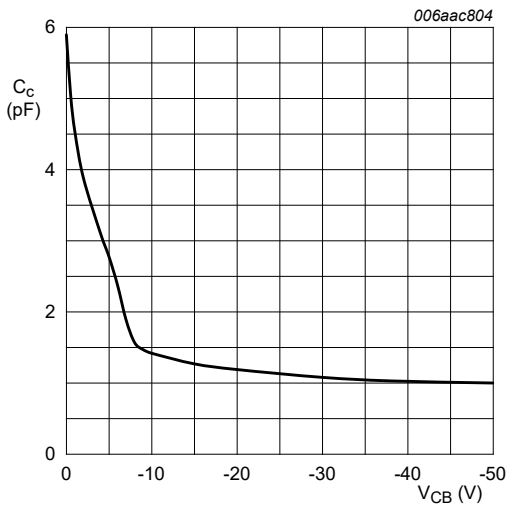
$V_{CE} = -0.3 \text{ V}$
 (1) $T_{amb} = -40 \text{ }^\circ\text{C}$
 (2) $T_{amb} = 25 \text{ }^\circ\text{C}$
 (3) $T_{amb} = 100 \text{ }^\circ\text{C}$

Fig. 11. TR2 (PNP): On-state input voltage as a function of collector current; typical values



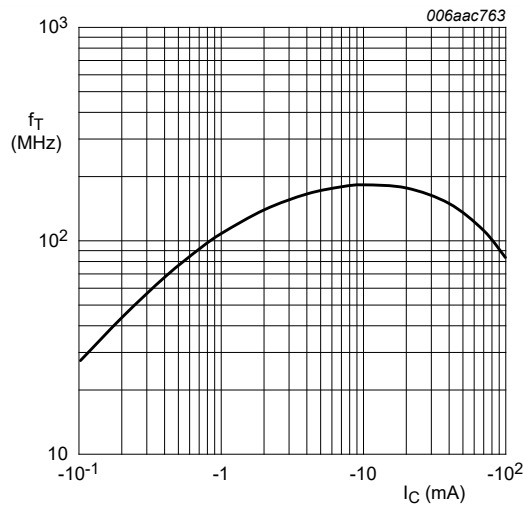
$V_{CE} = -5 \text{ V}$
 (1) $T_{amb} = -40 \text{ }^\circ\text{C}$
 (2) $T_{amb} = 25 \text{ }^\circ\text{C}$
 (3) $T_{amb} = 100 \text{ }^\circ\text{C}$

Fig. 12. TR2 (PNP): Off-state input voltage as a function of collector current; typical values



$f = 1 \text{ MHz}; T_{amb} = 25 \text{ }^\circ\text{C}$

Fig. 13. TR2 (PNP): Collector capacitance as a function of collector-base voltage; typical values



$f = 100 \text{ MHz}$
 $T_{amb} = 25 \text{ }^\circ\text{C}$
 $V_{CE} = -5 \text{ V}$

Fig. 14. TR2 (PNP): Transition frequency as a function of collector current; typical values of built-in transistor

11. Test information

Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

Resistor calculation

- Calculation of bias resistor 1 (R1)

$$R_1 = \frac{V(I_2) - V(I_1)}{I_2 - I_1}$$

- Calculation of bias resistor ratio (R2/R1)

$$\frac{R_2}{R_1} = \frac{V(I_4) - V(I_3)}{R_1 \cdot (I_4 - I_3)} - 1$$

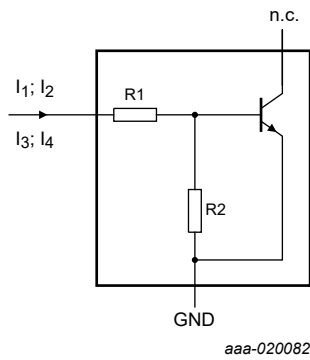


Fig. 15. TR1 (NPN): Resistor test circuit

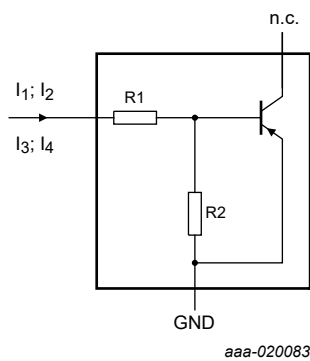


Fig. 16. TR2 (PNP): Resistor test circuit

Resistor test conditions

Table 8. Resistor test conditions

PIMD2	R1 (kΩ)	R2 (kΩ)	Test conditions			
			I ₁	I ₂	I ₃	I ₄
TR1 (NPN)	22	22	150 μA	230 μA	-150 μA	-230 μA
TR2 (PNP)	22	22	-150 μA	-230 μA	150 μA	230 μA

12. Package outline

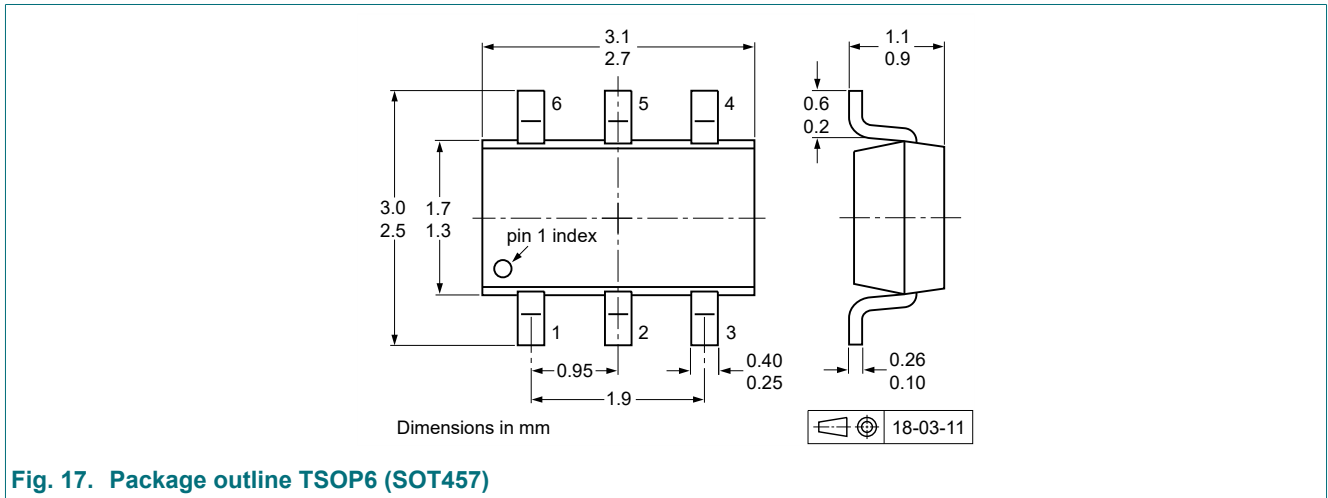


Fig. 17. Package outline TSOP6 (SOT457)

13. Soldering

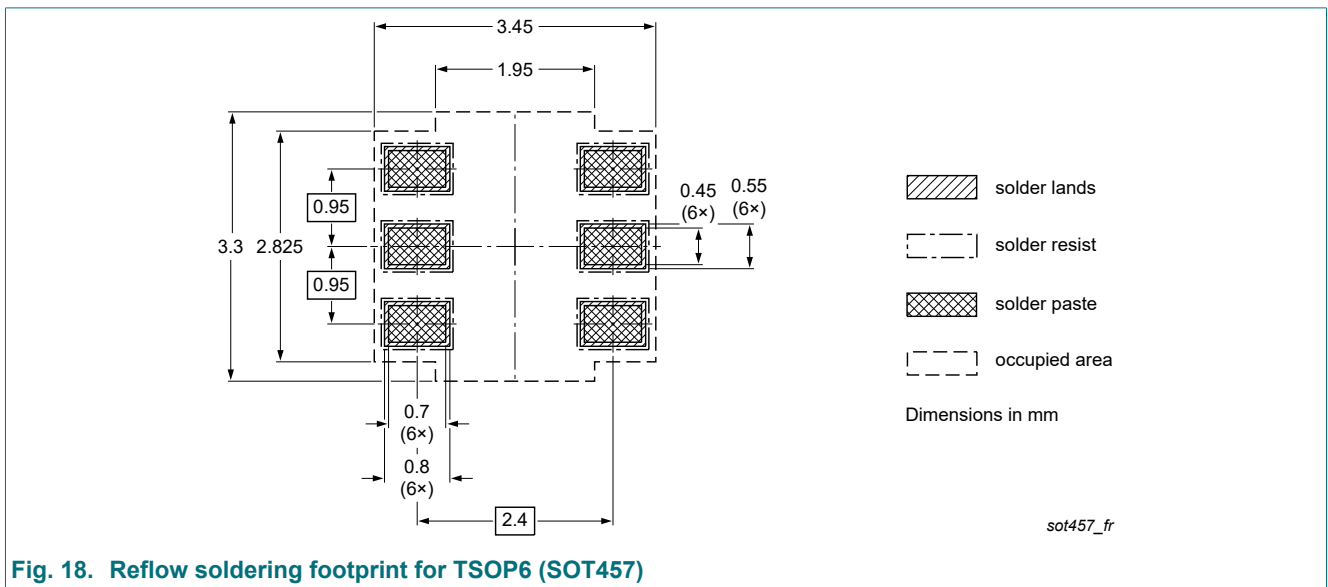


Fig. 18. Reflow soldering footprint for TSOP6 (SOT457)

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 22 kΩ, R2 = 22 kΩ

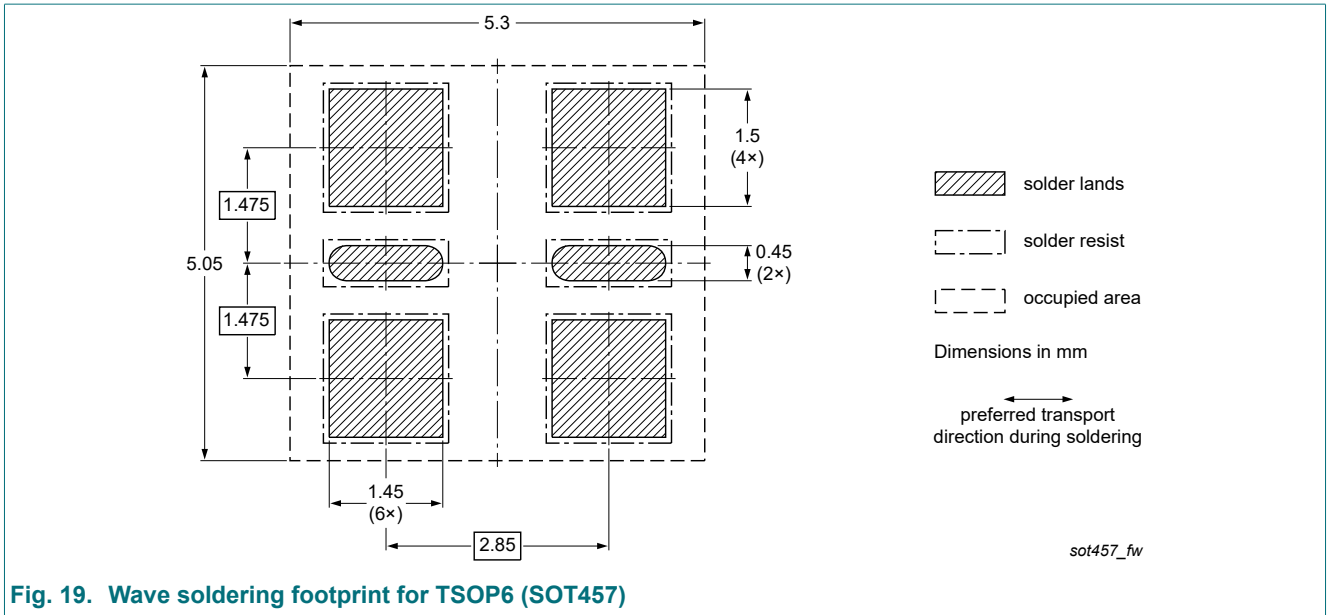


Fig. 19. Wave soldering footprint for TSOP6 (SOT457)

14. Revision history

Table 9. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PIMD2 v.9	20230313	Product data sheet	-	PEMD2_PIMD2_PUMD2 v.8
Modifications:	<ul style="list-style-type: none"> The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia. Legal texts have been adapted to the new company name where appropriate. Family data sheet splitted to single type data sheets. 			
PEMD2_PIMD2_PUMD2 v.8	20131114	Product data sheet	-	PEMD2_PIMD2_PUMD2 v.7
PEMD2_PIMD2_PUMD2 v.7	20080924	Product data sheet	-	PEMD2_PIMD2_PUMD2 v.6
PEMD2_PIMD2_PUMD2 v.6	20042104	Product specification	-	PEMD2_PIMD2_PUMD2 v.5
PEMD2_PIMD2_PUMD2 v.5	20030606	Product specification	-	-

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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